

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 6103555 A	20000815	5	Method of improving the reliability of low-voltage programmable antifuse	438/131	438/600; 438/762; 438/769; 438/956	Choi, Jeong Yeol
2	US 5196724 A	19930323	11	Programmable interconnect structures and programmable integrated circuits	257/530	257/50; 257/751; 257/764	Gordon, Kathryn E. et al.

from Spec

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 5391518 A	19950221	11	Method of making a field programmable read only memory (ROM) cell using an amorphous silicon fuse with buried contact polysilicon and metal electrodes	438/281	148/DIG.1; 438/132; 438/601	Bhushan, Bharat
2	US 5328865 A	19940712	9	Method for making cusp-free anti-fuse structures	438/600	438/627	Boardman, William J. et al.
3	US 5290734 A	19940301	11	Method for making anti-fuse structures	438/600	148/DIG.1; 148/DIG.55; 257/530; 438/639; 438/647	Boardman, William J. et al.
4	US 5210598 A	19930511	8	Semiconductor element having a resistance state transition region of two-layer structure	257/530		Nakazaki, Yasunori et al.
5	US 6249010 B1	20010619	11	Dielectric-based anti-fuse cell with polysilicon contact plug and method for its manufacture	257/50	257/530	Bergemont, Albert et al.
6	US 6242335 B1	20010605	10	Method for fabricating isolated anti-fuse structure	438/600	438/131; 438/467	Sher, Joseph C. et al.
7	US RE36893 E	20001003	9	Anti-fuse structure for reducing contamination of the anti-fuse material	257/530	257/50; 257/751; 257/752; 257/764	Pramanik, Dipankar et al.
8	US 5789795 A	19980804	10	Methods and apparatus for fabricating anti-fuse devices	257/530	438/131	Sanchez, Ivan et al.
9	US 5521423 A	19960528	18	Dielectric structure for anti-fuse programming element	257/530	257/209; 257/50; 257/529	Shinriki, Hiroshi et al.
10	US 5412244 A	19950502	15	Electrically-programmable low-impedance anti-fuse element	257/530	257/50; 257/607	Hamdy, Esmat Z. et al.
11	US 5365105 A	19941115	9	Sidewall anti-fuse structure and method for making	257/530	257/390; 365/96	Liu, David K. et al.
12	US 5266829 A	19931130	13	Electrically-programmable low-impedance anti-fuse element	257/530		Hamdy, Esmat Z. et al.
13	US 4943538 A	19900724	9	Programmable low impedance anti-fuse element	438/215	438/333; 438/467; 438/600	Mohsen, Amr M. et al.
14	US 4823181 A	19890418	11	Programmable low impedance anti-fuse element	257/530	257/296; 257/640; 365/96	Mohsen, Amr M. et al.

P145

PLUS Search Results for S/N 09/682,628, Searched June 26, 2002 (Top 50)

5903041	5774011	5978248	5434448	6124165
6156588	5789795	6016001	5493146	RE36893
6240033	6061264	6021079	5521423	6140692
5793094	6096580	6233194	5572458	6159836
5210598	6174797	4823181	5573970	6242335
5416355	5278784	4899205	5625219	6249010
5290734	5365105	5266829	5625220	4876220
5328865	5427979	5331196	6060785	4881114
5391518	5565703	5391513	6096571	4943538
5672994	5742555	5412244	6124194	5365104

Most Frequently Occurring Classifications of Patents Returned
From A Search of 09/682,628 on June 26, 2002

Combined Classifications

28 257/530
14 438/600
13 257/50
10 365/96
7 365/225.7
7 438/131
7 438/467
6 257/529
4 438/132
3 148/DIG 55
3 257/209
3 365/103
3 438/215
2 148/DIG 1
2 257/751
2 257/752
2 257/764
2 327/525
2 438/281
2 438/601
2 438/624

-
- 28 257/530 (19 OR, 9 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/499 INTEGRATED CIRCUIT STRUCTURE WITH ELECTRICALLY
ISOLATED COMPONENTS
257/528 .Passive components in ICs
257/529 ..Including programmable passive component
(e.g., fuse)
257/530 ...Anti-fuse
- 14 438/600 (8 OR, 6 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY
CONDUCTIVE MATERIAL
438/597 .To form ohmic contact to semiconductive
material
438/598 ..Selectively interconnecting (e.g.,
customization, wafer scale integration, etc.)
438/600 ...Using structure alterable to conductive
state (i.e., antifuse)
- 13 257/50 (1 OR, 12 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/49 NON-SINGLE CRYSTAL, OR RECRYSTALLIZED,
SEMICONDUCTOR MATERIAL FORMS PART OF ACTIVE JUNCTION
(INCLUDING FIELD-INDUCED ACTIVE JUNCTION)
257/50 .Non-single crystal, or recrystallized, active
junction adapted to be electrically shorted (e.g.,
"anti-fuse" element)
- 10 365/96 (4 OR, 6 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/94 READ ONLY SYSTEMS (I.E.. SEMIPERMANENT)
365/96 .Fusible
- 7 365/225.7 (4 OR, 3 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/189.01 READ/WRITE CIRCUIT
365/225.7 .Having fuse element
- 7 438/131 (1 OR, 6 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/128 MAKING DEVICE ARRAY AND SELECTIVELY
INTERCONNECTING
438/131 .Using structure alterable to conductive state
(i.e., antifuse)
- 7 438/467 (0 OR, 7 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/466 DIRECT APPLICATION OF ELECTRICAL CURRENT
438/467 .To alter conductivity of fuse or antifuse
element